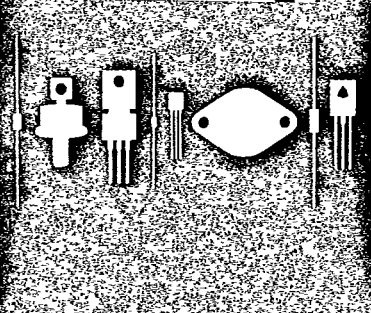


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MJ12010

D

NPN SILICON TRANSISTOR

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJ12010 type is a Silicon NPN Power Transistor mounted in a hermetically sealed metal case designed for Horizontal Deflection Circuits.

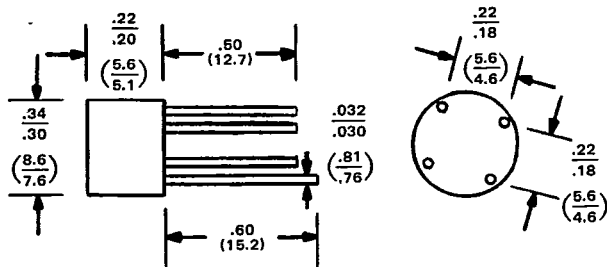
MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$)

Collector-Emitter Voltage	V_{CE}	950	V
Collector-Emitter Voltage	V_{CE0}	400	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	10	A
Emitter Current	I_E	15	A
Base Current	I_B	5.0	A
Power Dissipation	P_D	100	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 TO +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JC}	1.25	$^{\circ}\text{C/W}$

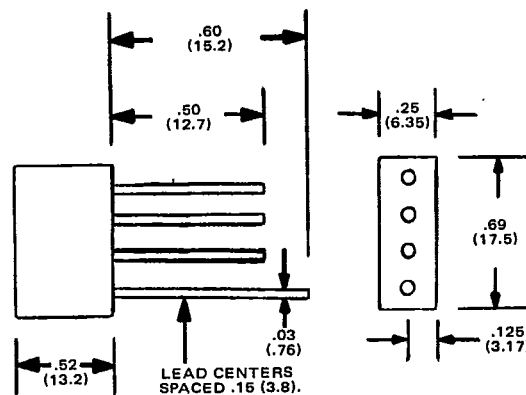
ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CES}	$V_{CE}=950\text{V}$		1.0	mA
I_{EBO}	$V_{BE}=5.0\text{V}$		1.0	mA
BV_{CEO}	$I_C=50\text{mA}$	400		V
$V_{CE}(\text{SAT})$	$I_C=5.0\text{A}, I_B=1.2\text{A}$		5.0	V
$V_{BE}(\text{SAT})$	$I_C=5.0\text{A}, I_B=1.2\text{A}$		1.5	V
f_T	$V_{CE}=5.0\text{V}, I_C=0.1\text{A}, f=1.0\text{MHz}$	10TYP		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$	160TYP		pF
t_f	$I_C=5.0\text{A}, I_{B1}=1.2\text{A}, L_B=8.0\mu\text{H}$		1.0	μs
$I_{s/b}$	$V_{CE}=40\text{V}, t=1.0\text{s}$	2.5		A

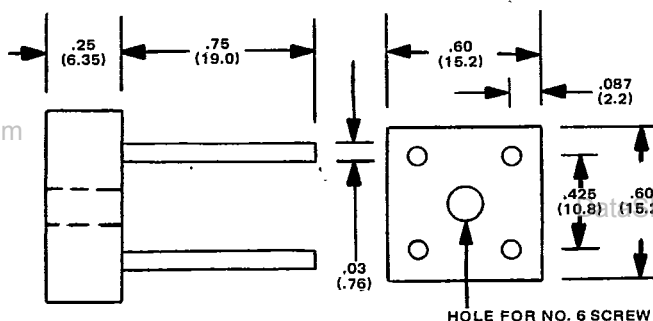
CASE OUTLINE DRAWINGS

**CASE A**

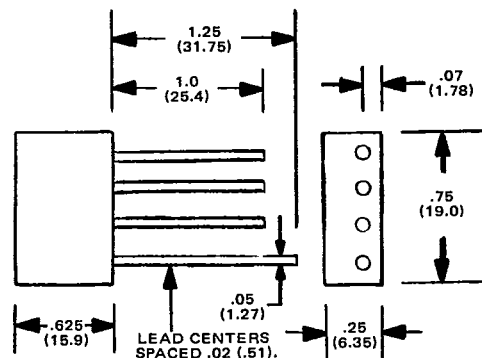
CBR1 Series
CBR2 Series

**CASE B**

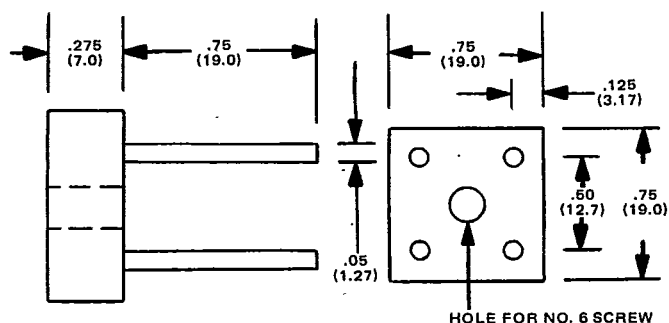
CBR1-L Series
CBR2-L Series

**CASE C**

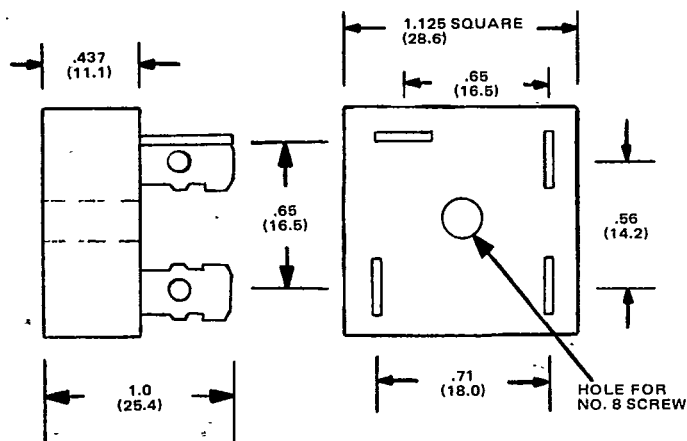
CBR3-P Series

**CASE D**

CBR4-L Series

**CASE E**

CBR8 Series

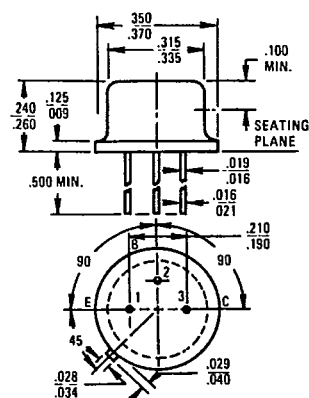
**CASE F**

CBR10 Series, CBR25 Series
CBR12 Series, CBR30 Series

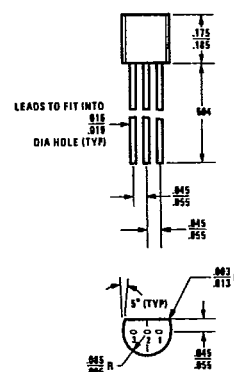
All Dimensions in Inches (Millimeters)

Drawings Not To Scale

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TO-39

TO-92



TO-106

